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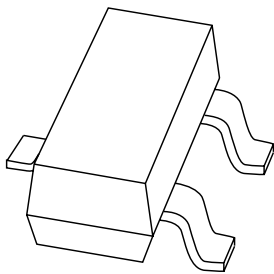
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Kind regards,

Team Nexperia

DATA SHEET



MMBT2222A NPN switching transistor

Product data sheet
Supersedes data of 2000 Apr 11

2004 Jan 16

NPN switching transistor

MMBT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package.
PNP complement: PMBT2907A.

MARKING

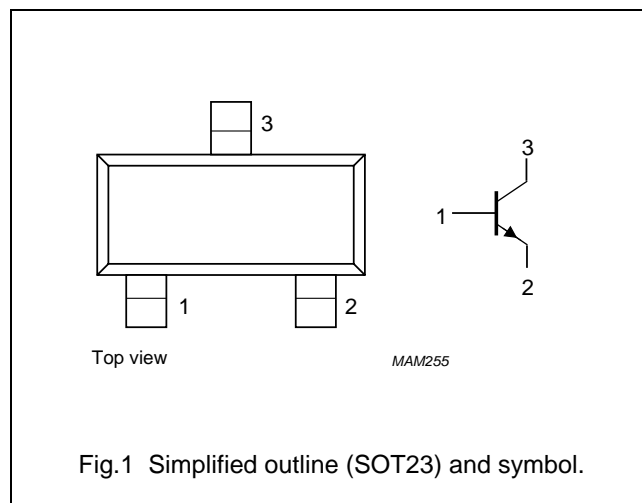
| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|
| MMBT2222A | 7C* |

Note

1. * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | |
|-------------|---------|--|---------|
| | NAME | DESCRIPTION | VERSION |
| MMBT2222A | – | plastic surface mounted package; 3 leads | SOT23 |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|-------------------------------|--|------|------|--------------------|
| V_{CBO} | collector-base voltage | open emitter | – | 75 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 40 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 6 | V |
| I_C | collector current (DC) | | – | 600 | mA |
| I_{CM} | peak collector current | | – | 800 | mA |
| I_{BM} | peak base current | | – | 200 | mA |
| P_{tot} | total power dissipation | $T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 1 | – | 250 | mW |
| T_{stg} | storage temperature | | –65 | +150 | $^{\circ}\text{C}$ |
| T_j | junction temperature | | – | 150 | $^{\circ}\text{C}$ |
| T_{amb} | operating ambient temperature | | –65 | +150 | $^{\circ}\text{C}$ |

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

MMBT2222A

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

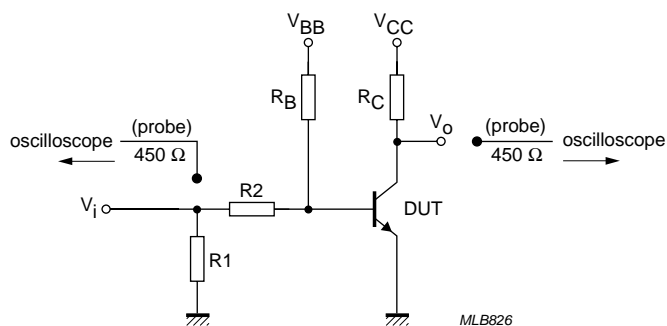
| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--|--------------------------------------|---|------|------|---------------|
| I_{CBO} | collector cut-off current | $I_E = 0$; $V_{CB} = 60\text{ V}$ | – | 10 | nA |
| | | $I_E = 0$; $V_{CB} = 60\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$ | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0$; $V_{EB} = 5\text{ V}$ | – | 10 | nA |
| h_{FE} | DC current gain | $I_C = 0.1\text{ mA}$; $V_{CE} = 10\text{ V}$ | 35 | – | |
| | | $I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$ | 50 | – | |
| | | $I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$ | 75 | – | |
| | | $I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = -55\text{ }^{\circ}\text{C}$ | 35 | – | |
| | | $I_C = 150\text{ mA}$; $V_{CE} = 10\text{ V}$ | 100 | 300 | |
| | | $I_C = 150\text{ mA}$; $V_{CE} = 1\text{ V}$ | 50 | – | |
| | | $I_C = 500\text{ mA}$; $V_{CE} = 10\text{ V}$ | 40 | – | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1 | – | 300 | mV |
| | | $I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1 | – | 1 | V |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1 | 0.6 | 1.2 | V |
| | | $I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1 | – | 2 | V |
| C_c | collector capacitance | $I_E = i_e = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$ | – | 8 | pF |
| C_e | emitter capacitance | $I_C = i_c = 0$; $V_{EB} = 500\text{ mV}$; $f = 1\text{ MHz}$ | – | 25 | pF |
| f_T | transition frequency | $I_C = 20\text{ mA}$; $V_{CE} = 20\text{ V}$; $f = 100\text{ MHz}$ | 300 | – | MHz |
| F | noise figure | $I_C = 100\text{ }\mu\text{A}$; $V_{CE} = 5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 1\text{ kHz}$ | – | 4 | dB |
| Switching times (between 10% and 90% levels); (see Fig.2) | | | | | |
| t_{on} | turn-on time | $I_{Con} = 150\text{ mA}$; $I_{Bon} = 15\text{ mA}$; $I_{Boff} = -15\text{ mA}$ | – | 35 | ns |
| t_d | delay time | | – | 15 | ns |
| t_r | rise time | | – | 20 | ns |
| t_{off} | turn-off time | | – | 250 | ns |
| t_s | storage time | | – | 200 | ns |
| t_f | fall time | | – | 60 | ns |

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN switching transistor

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$V_i = 9.5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R1 = 68 \text{ } \Omega$; $R2 = 325 \text{ } \Omega$; $R_B = 325 \text{ } \Omega$; $R_C = 160 \text{ } \Omega$.
 $V_{BB} = -3.5 \text{ V}$; $V_{CC} = 29.5 \text{ V}$.
Oscilloscope: input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

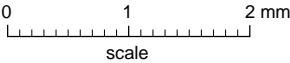
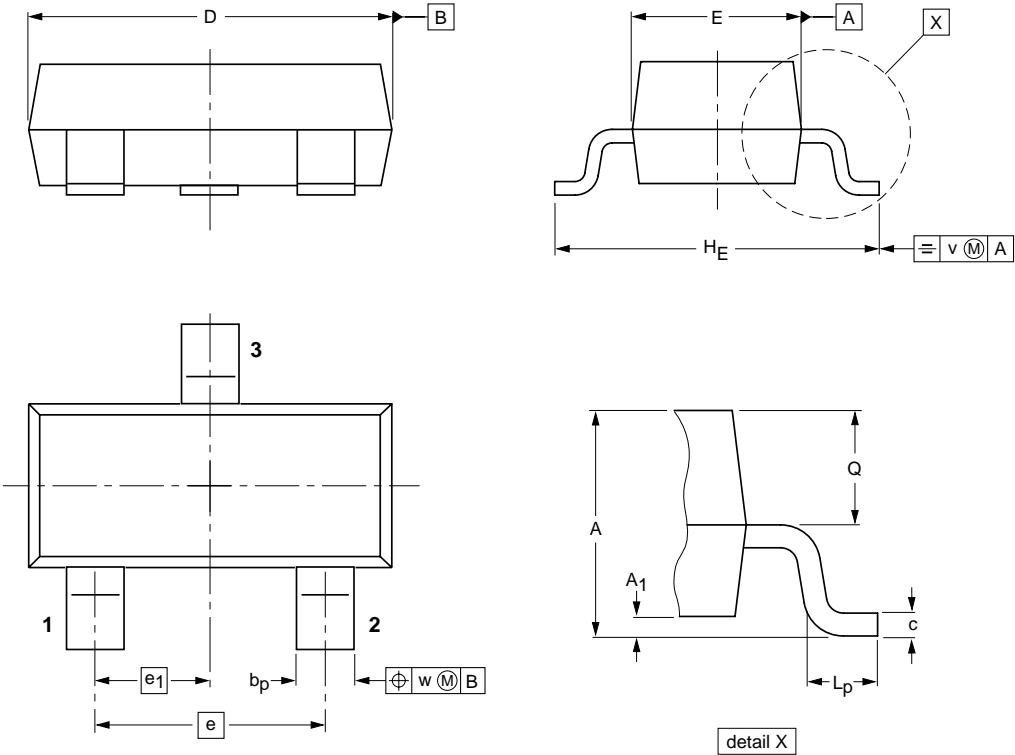
NPN switching transistor

MMBT2222A

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ max. | b _p | c | D | E | e | e ₁ | H _E | L _p | Q | v | w |
|------|------------|------------------------|----------------|--------------|------------|------------|-----|----------------|----------------|----------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|----------|-------|--|------------------------|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT23 | | TO-236AB | | | | 04-11-04 06-03-16 |

NPN switching transistor

MMBT2222A

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

Customer notification

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